

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

Claim 1 (Currently amended): A process chamber for use in fabricating semiconductor devices, comprising:

a vessel into which a process gas is to be supplied;

an upper electrode disposed in an upper part of said vessel and to which power is to be applied;

a shield ring extending along an outer peripheral side surface of the upper electrode for insulating the upper electrode;

a lower electrode disposed under the upper electrode as spaced from the upper electrode and to which power is to be applied to convert the process gas to plasma;

an electrostatic chuck disposed on said lower electrode and on which a wafer is to be received;

a focus ring extending along an outer peripheral surface of the electrostatic chuck and by which reactive ions of the plasma are directed toward the wafer; and

an insulation ring unit disposed under said focus ring and extending along an the outer peripheral side surface of the lower electrode for insulating the lower electrode,

wherein said shield ring and said insulation ring unit each include a substrate, and a protection layer coating the substrate to prevent the shield ring and the insulation ring unit from being etched by the plasma.

Claim 2 (Original): The process chamber according to claim 1, wherein said protection layer is a layer of AlN.

Claim 3 (Currently amended): The process chamber according to claim 1, ~~wherein~~ wherein said protection layer is a layer of TiN.

Claim 4 (Currently amended): The process chamber according to claim 1, ~~wherein~~ wherein said protection layer is a diamond-like coating (DLC).

Claim 5 (Currently amended): The ~~process~~ process chamber according to claim 1, wherein the protection layer is a layer of Al₂O₃.

Claim 6 (New): The process chamber according to claim 1, wherein said focus ring is of aluminum.

Claim 7 (New): The process chamber according to claim 1, wherein the substrate of the insulation ring unit is a quartz substrate.

Claim 8 (New): The process chamber according to claim 6, wherein the substrate of the insulation ring unit is a quartz substrate.

Claim 9 (New): The process chamber according to claim 7, wherein said protection layer is selected from the group consisting of a layer of TiN, a diamond-like coating (DLC), and a layer Al_2O_3 .

Claim 10 (New): The process chamber according to claim 8, wherein said protection layer is selected from the group consisting of a layer of TiN, a diamond-like coating (DLC), and a layer Al_2O_3 .